

**FEATURE**

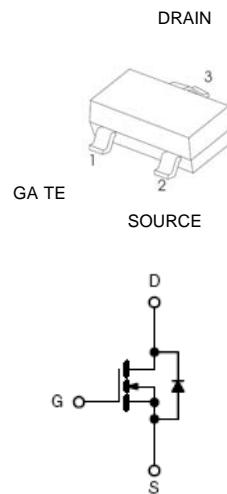
- TrenchFET Power MOSFET

**APPLICATIONS**

- Load Switch for Portable Devices
- DC/DC Converter

**MARKING**

- MARKING: 2302

**SOT-23****Maximum ratings (Ta=25°C unless otherwise noted)**

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	20	V
Gate-Source Voltage	V <sub>GS</sub>	±8	
Continuous Drain Current	I <sub>D</sub>	2.3	A
Continuous Source-Drain Current(Diode Conduction)	I <sub>S</sub>	0.6	
Power Dissipation	P <sub>D</sub>	0.35	W
Thermal Resistance from Junction to Ambient (t≤5s)	R <sub>θJA</sub>	357	°C/W
Operating Junction	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55 ~+150	



## Electrical characteristics (Ta=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Static</b>						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10µA	20			V
Gate-threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 50µA	0.65	0.95	1.2	
Gate-body leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±8V			±100	nA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V			1	µA
Drain-source on-resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 2.5A		0.055	0.085	Ω
		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 2.1A		0.070	0.125	
Forward transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 5V, I <sub>D</sub> = 2.5A		8		S
Diode forward voltage	V <sub>SD</sub>	I <sub>S</sub> =0.94A, V <sub>GS</sub> =0V		0.76	1.2	V
<b>Dynamic</b>						
Total gate charge	Q <sub>g</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 2.5A		4.0	10	nC
Gate-source charge	Q <sub>gs</sub>			0.65		
Gate-drain charge	Q <sub>gd</sub>			1.5		
Input capacitance <sup>b</sup>	C <sub>iss</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1MHz		300		pF
Output capacitance <sup>b</sup>	C <sub>oss</sub>			120		
Reverse transfer capacitance <sup>b</sup>	C <sub>rss</sub>			80		
<b>Switching<sup>b</sup></b>						
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = 10V, R <sub>L</sub> = 5.5Ω, I <sub>D</sub> ≈ 2.5A, V <sub>GEN</sub> = 4.5V, R <sub>g</sub> = 6Ω		7	15	ns
Rise time	t <sub>r</sub>			55	80	
Turn-off delay time	t <sub>d(off)</sub>			16	60	
Fall time	t <sub>f</sub>			10	25	

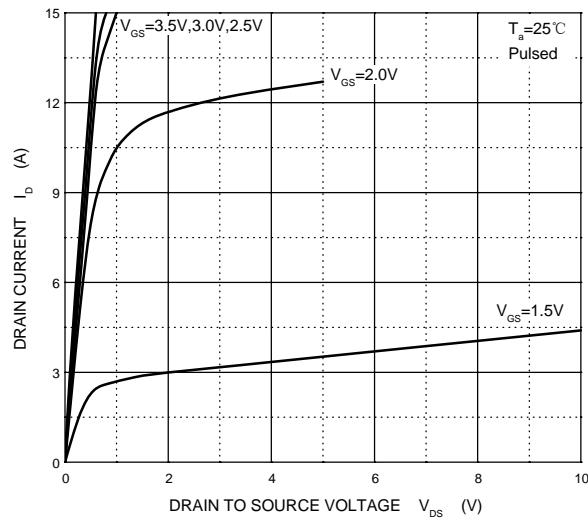
Notes :

a. Pulse Test : Pulse width ≤ 300µs, duty cycle ≤ 2%.

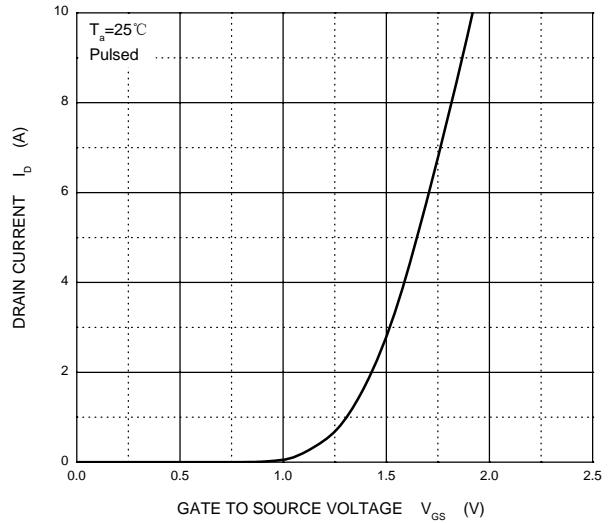
b. These parameters have no way to verify.

## Typical Characteristics

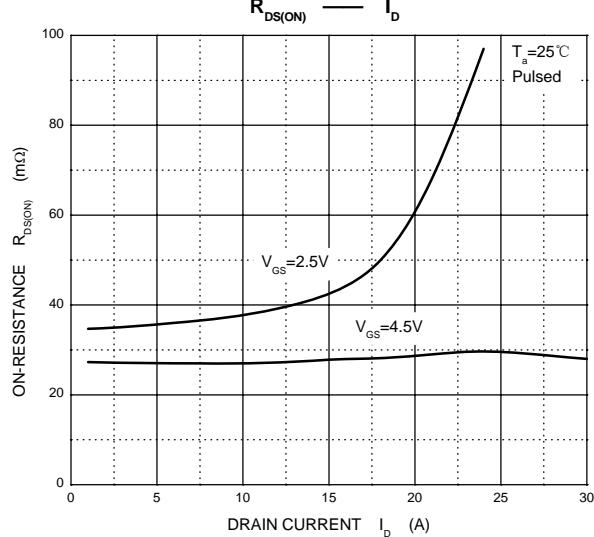
**Output Characteristics**



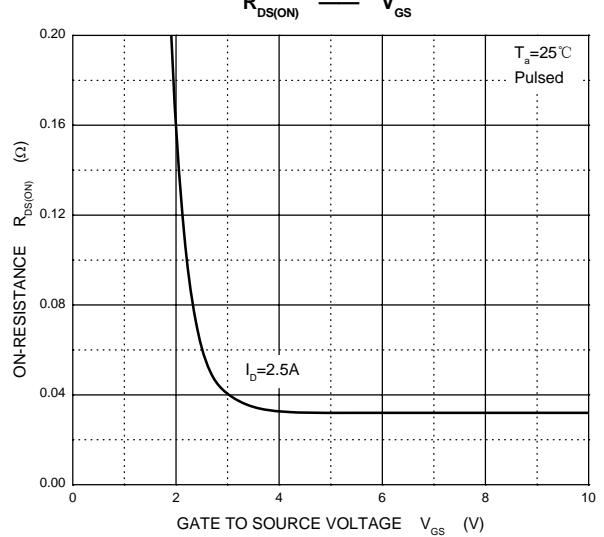
**Transfer Characteristics**



$R_{DS(ON)}$  —  $I_D$



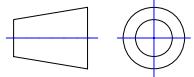
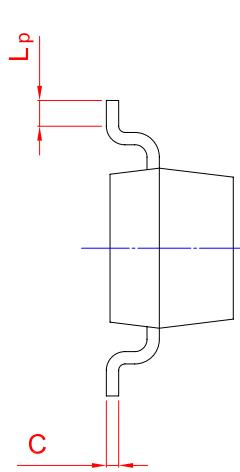
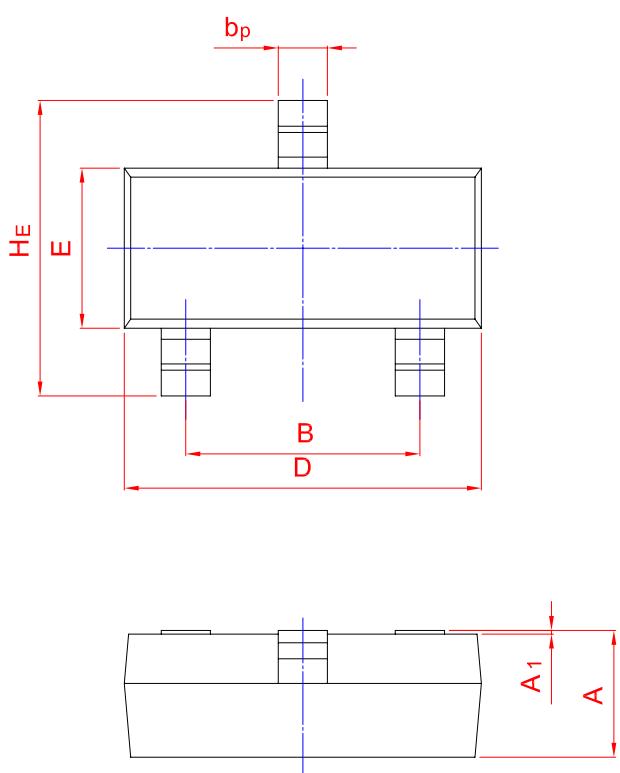
$R_{DS(ON)}$  —  $V_{GS}$



## PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	bp	C	D	E	He	A1	Lp
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20